

P-Channel 20-V (D-S) MOSFET

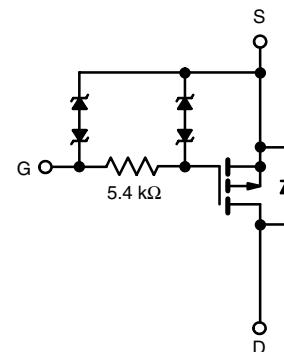
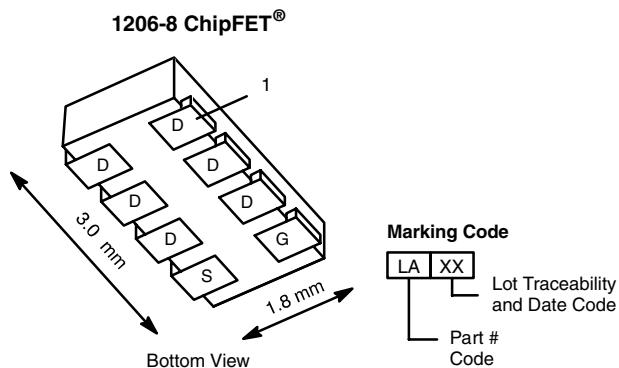
PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 20	0.045 at $V_{GS} = - 4.5$ V	- 6.2
	0.060 at $V_{GS} = - 2.5$ V	- 5.4
	0.082 at $V_{GS} = - 1.8$ V	- 4.6

FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- ESD Protected^b 5000 V



RoHS
COMPLIANT
HALOGEN
FREE
Available



Ordering Information: Si5461EDC-T1-E3 (Lead (Pb)-free)
Si5461EDC-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	V_{DS}		- 20		
Gate-Source Voltage	V_{GS}		± 12		V
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	- 6.2	- 4.5		A
		- 4.5	- 3.2		
Pulsed Drain Current	I_{DM}		- 20		
Continuous Source Current ^a	I_S	- 2.1	- 1.1		
Maximum Power Dissipation ^a	P_D	2.5	1.3		W
		1.3	0.7		
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150			
Soldering Recommendations (Peak Temperature) ^{c, d}		260		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	$t \leq 5$ s	40	50		°C/W
	Steady State	80	95		
Maximum Junction-to-Foot (Drain)	R_{thJF}	15	20		

Notes:

- Surface Mounted on 1" x 1" FR4 board.
- When using HBM. The MM rating is 300 V.
- See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted

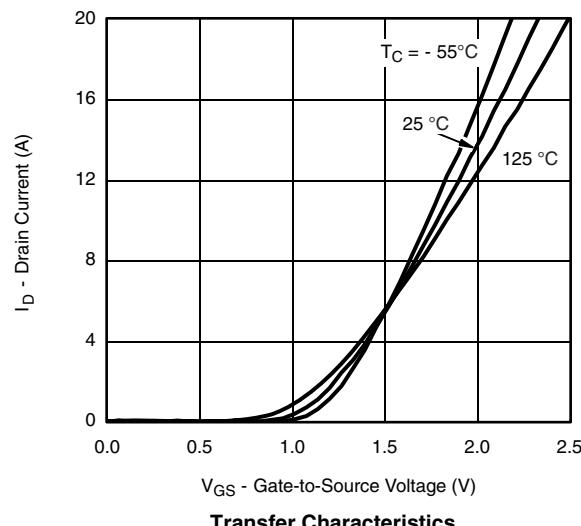
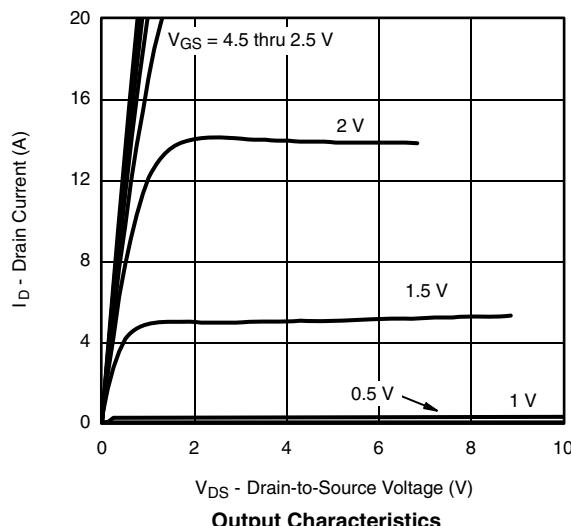
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu\text{A}$	-0.45			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 4.5 \text{ V}$			± 1.5	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -16 \text{ V}$, $V_{GS} = 0 \text{ V}$			-1	μA
		$V_{DS} = -16 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 85^\circ\text{C}$			-5	
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{DS} \leq -5 \text{ V}$, $V_{GS} = -4.5 \text{ V}$	-20			A
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = -4.5 \text{ V}$, $I_D = -5.0 \text{ A}$		0.037	0.045	Ω
		$V_{GS} = -2.5 \text{ V}$, $I_D = -4.0 \text{ A}$		0.050	0.060	
		$V_{GS} = -1.8 \text{ V}$, $I_D = -2 \text{ A}$		0.066	0.082	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -5 \text{ V}$, $I_D = -5.0 \text{ A}$		12		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.1 \text{ A}$, $V_{GS} = 0 \text{ V}$		-0.7	-1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -10 \text{ V}$, $V_{GS} = -4.5 \text{ V}$, $I_D = -5.0 \text{ A}$		12.5	20	nC
Gate-Source Charge	Q_{gs}			2.0		
Gate-Drain Charge	Q_{gd}			4.0		
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = -10 \text{ V}$, $R_L = 10 \Omega$ $I_D \geq -1 \text{ A}$, $V_{GEN} = -4.5 \text{ V}$, $R_G = 6 \Omega$		2.5	3.5	ns
Rise Time	t_r			4.5	8.0	
Turn-Off Delay Time	$t_{d(\text{off})}$			27	40	
Fall Time	t_f			15	25	

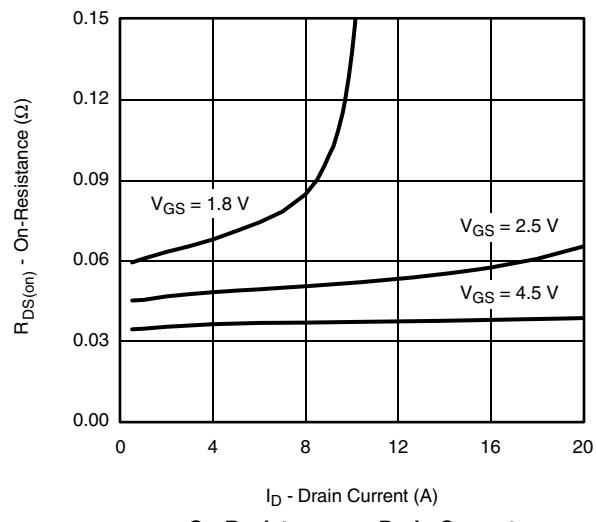
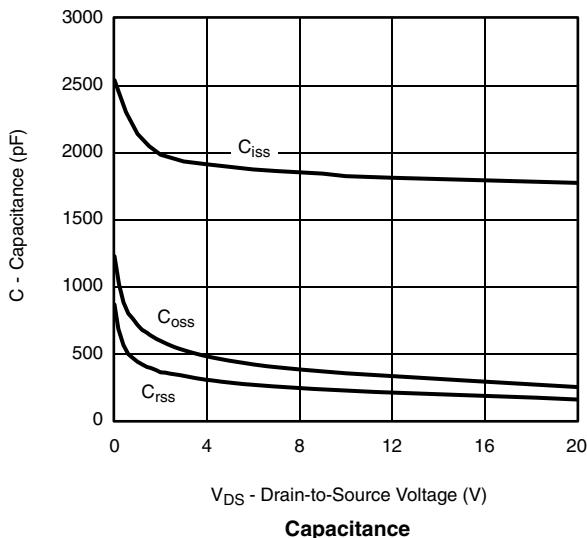
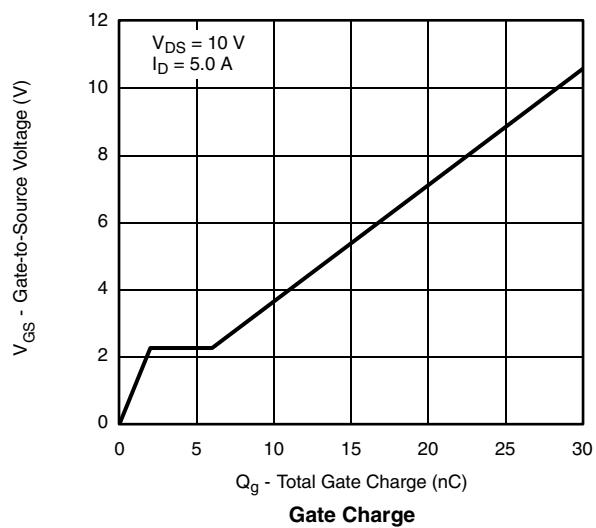
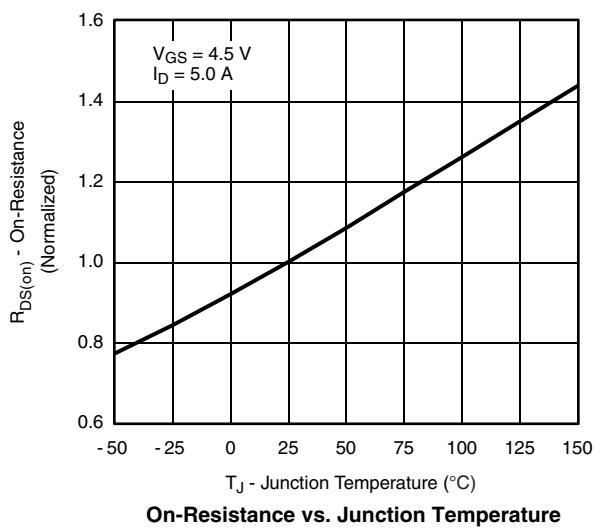
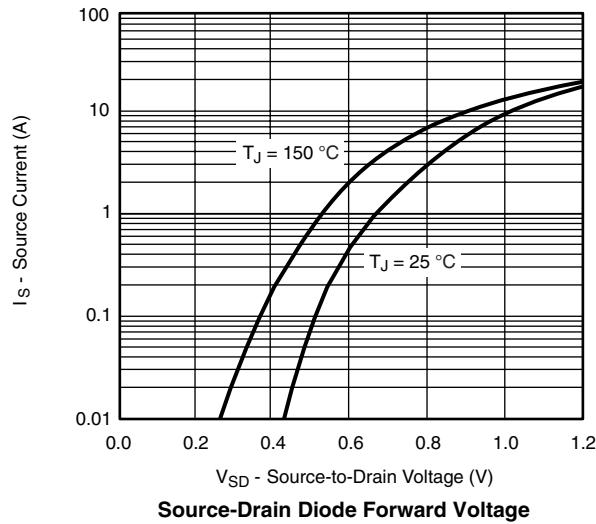
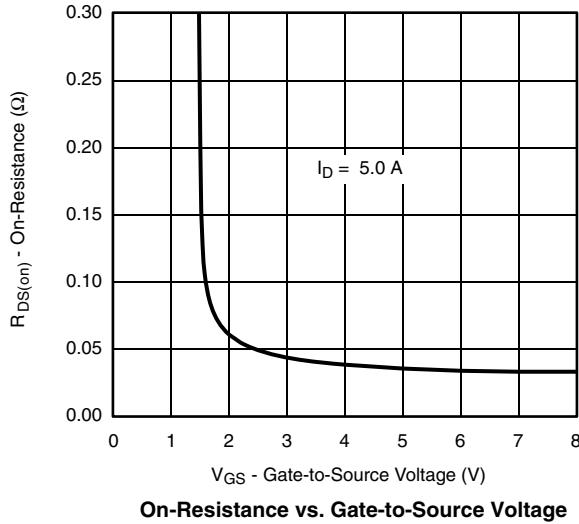
Notes:

a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.

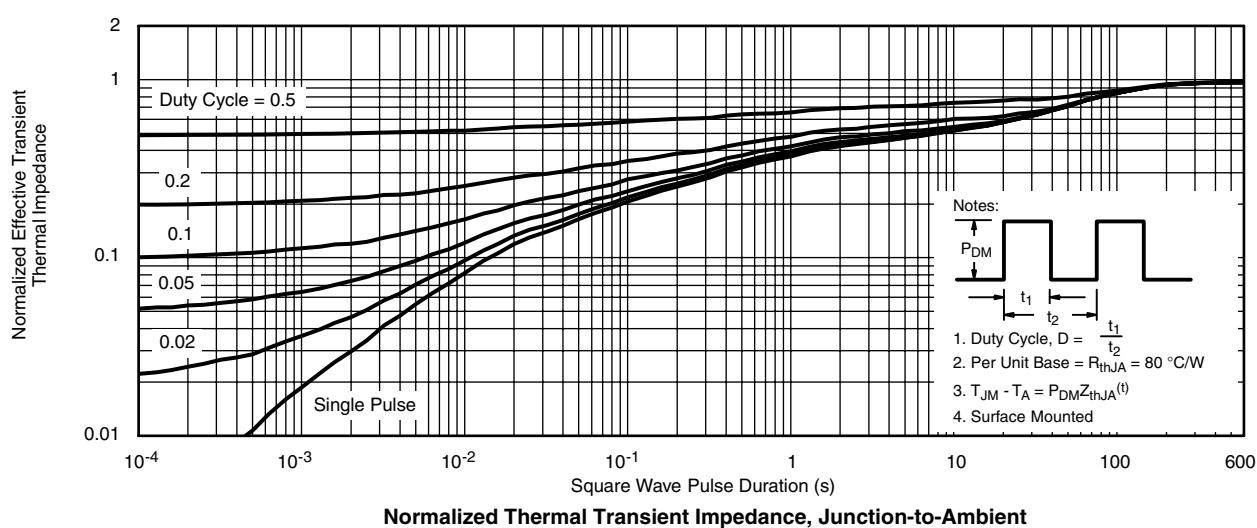
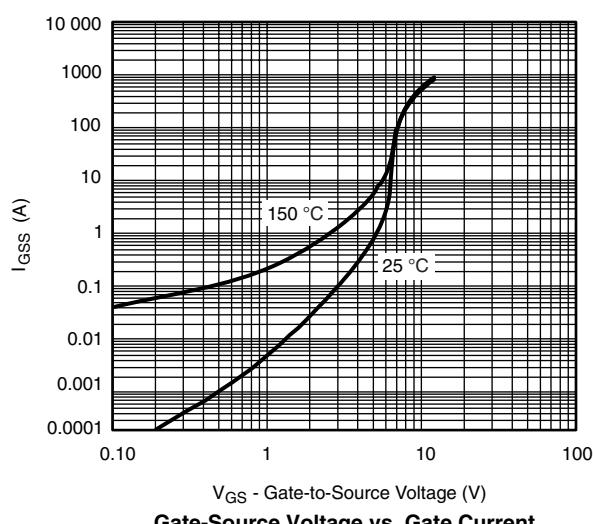
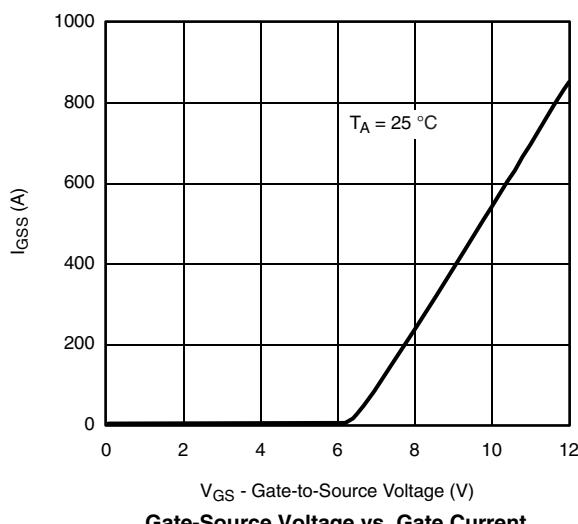
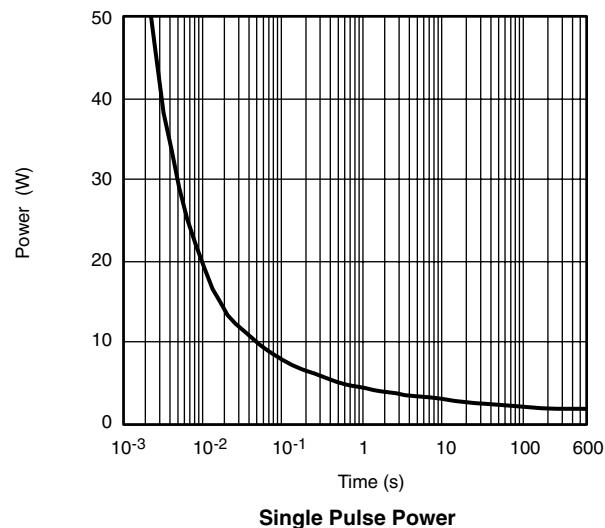
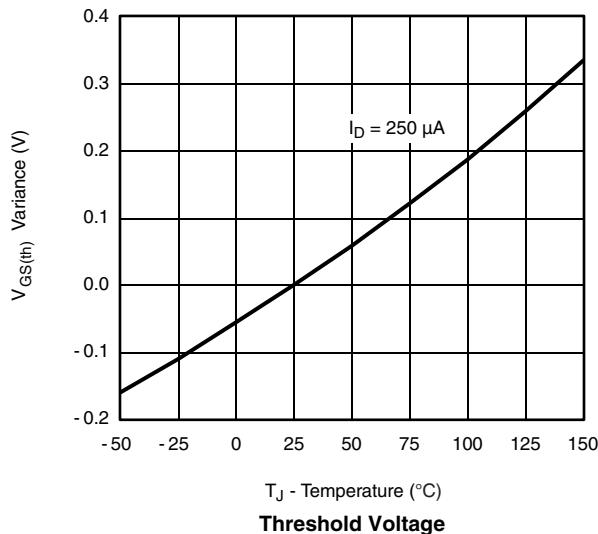
b. Guaranteed by design, not subject to production testing.

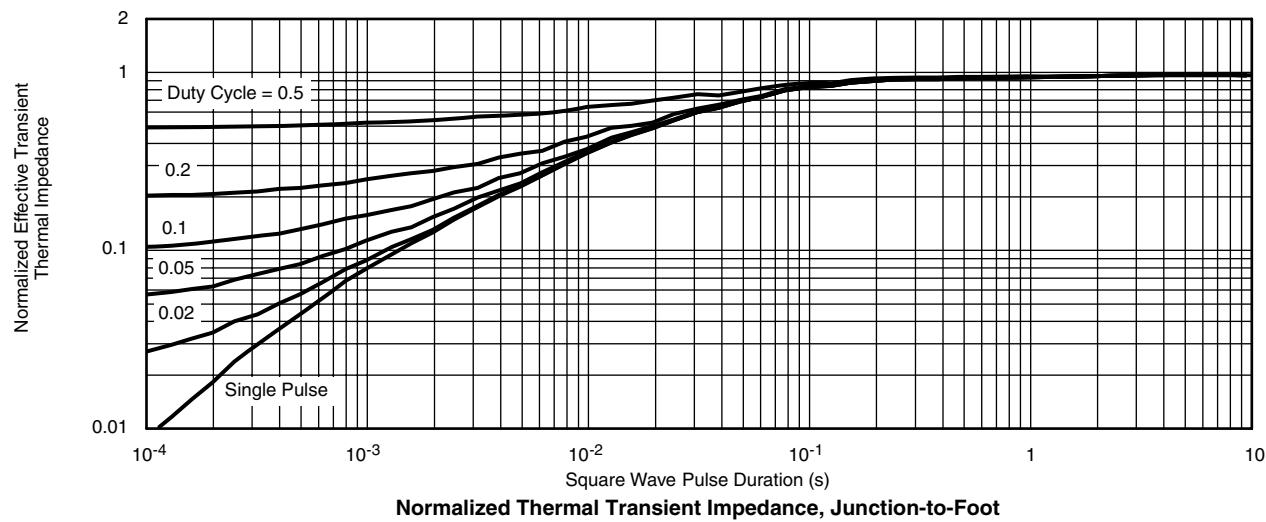
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25°C , unless otherwise noted

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On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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